



### N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>A</sub> = +25 ℃
	3.5Ω @ V <sub>GS</sub> = 10V	0.48A
240V	3.5Ω @ V <sub>GS</sub> = 4.5V	0.48A
	6.0Ω @ V <sub>GS</sub> = 3.3V	0.37A

### Description

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

# **Applications**

- DC-DC Converters
- Power Management Functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.



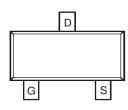
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

## **Mechanical Data**

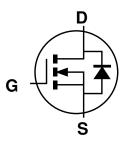
- Case: SOT23
- Case Material: Molded Plastic; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Solderable per MIL-STD-202, Method 208 @3
- Lead-Free Plating (Matte Tin Finish Annealed over Alloy 42 Leadframe).
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)



Top View



Top View Pin Configuration



Equivalent Circuit

### Ordering Information (Note 4)

Part Number	Case	Packaging
DMN24H3D5L-7	SOT23	3,000/Tape & Reel
DMN24H3D5L-13	SOT23	10,000/Tape & Reel

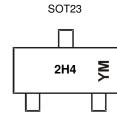
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



2H4 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: C = 2015) M = Month (ex: 9 = September)

Date	Code	Key

Notes:

Date Obuc Rey												
Year	2015		2016	2017		2018	2019		2020	2021		2022
Code	С		D	E		F	G		Н	l		J
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



#### **Maximum Ratings** (@T<sub>A</sub> = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V <sub>DSS</sub>	240	V		
Gate-Source Voltage	V <sub>GSS</sub>	±20	V		
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V Steady State		T <sub>A</sub> = +25 ℃ T <sub>A</sub> = +70 ℃	ID	0.48 0.39	A
Pulsed Drain Current (10µs pulse, duty cycle ≤ 1%)	I <sub>DM</sub>	1.9	А		
Maximum Body Diode Continuous Current (Note 6)			IS	1.5	А

### Thermal Characteristics (@T<sub>A</sub> = +25 °C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Total Power Dissipation	(Note 5)	Pn	0.76	W	
	(Note 6)	PD	1.26		
Thermal Desistance, Junction to Ambient	(Note 5)	n	163		
Thermal Resistance, Junction to Ambient	(Note 6)	R <sub>θJA</sub>	99	°C/W	
Thermal Resistance, Junction to Case	(Note 6)	R <sub>θJC</sub>	31		
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to 150	S	

## Electrical Characteristics (@T<sub>A</sub> = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						1
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	240			V	$V_{GS} = 0V, I_D = 250 \mu A$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_		1.0	μA	$V_{DS} = 192V, V_{GS} = 0V$
Gate-Body Leakage	I <sub>GSS</sub>	_		±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0	1.95	2.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
		_	1.5	3.5		$V_{GS} = 10V, I_D = 0.3A$
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	1.5	3.5	Ω	$V_{GS} = 4.5V, I_D = 0.2A$
		_	1.7	6.0		$V_{GS} = 3.3V, I_D = 0.1A$
Diode Forward Voltage	V <sub>SD</sub>	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 0.3A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C <sub>iss</sub>	_	188	_		
Output Capacitance	C <sub>oss</sub>	_	11	_	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	_	8	_		
Gate Resistance	Rg	_	3.86	_	Ω	VDS = 0V, VGS = 0V, f = 1.0MHz
Total Gate Charge	Qg	_	6.6	_		
Gate-Source Charge	Q <sub>gs</sub>	_	0.8	_	nC	$V_{DS} = 192V, V_{GS} = 10V,$ $I_{D} = 0.5A$
Gate-Drain Charge	Q <sub>gd</sub>	_	2.1	_		$I_D = 0.3A$
Turn-On Delay Time	t <sub>D(on)</sub>	_	2.3	_		
Turn-On Rise Time	tr	_	2.0	_	nS	$V_{DS} = 60V, R_{L} = 200\Omega$
Turn-Off Delay Time	t <sub>D(off)</sub>		21		113	$V_{GS}$ = 10V, $R_G$ = 25 $\Omega$
Turn-Off Fall Time	t <sub>f</sub>	_	7.2	_	1	

5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper pad layout

7 .Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to production testing.

Notes:





= 85 ℃

= 25 ℃

-55 ℃

3.5

T<sub>A</sub> = 125 ℃

T<sub>A</sub> = -55 ℃

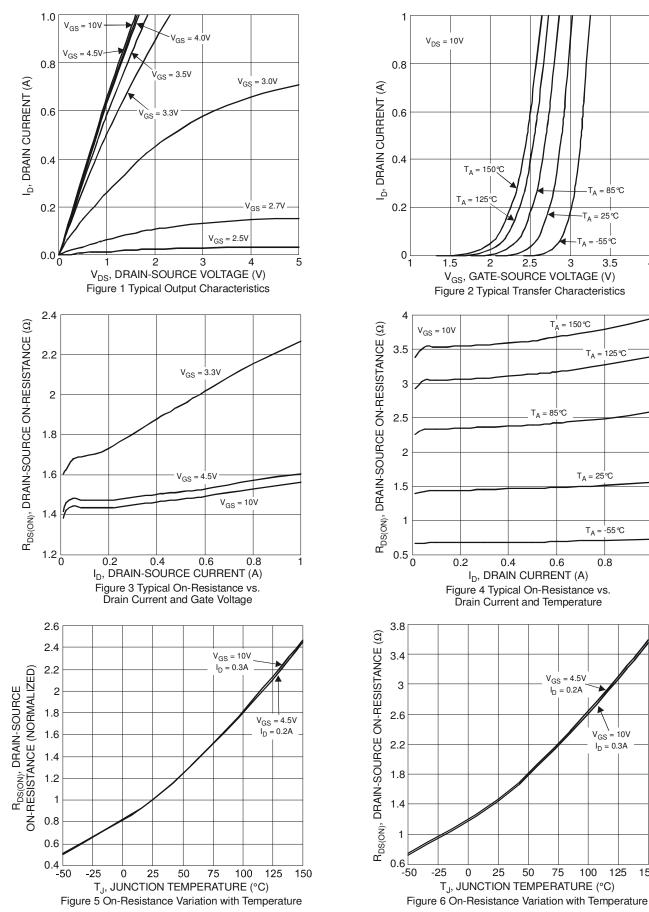
0.8

 $V_{GS} = 10V$  $I_D = 0.3A$ 

125

1

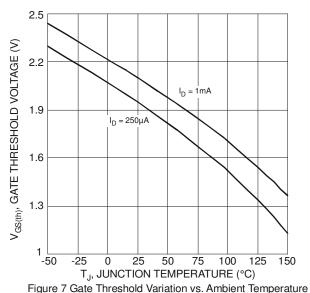
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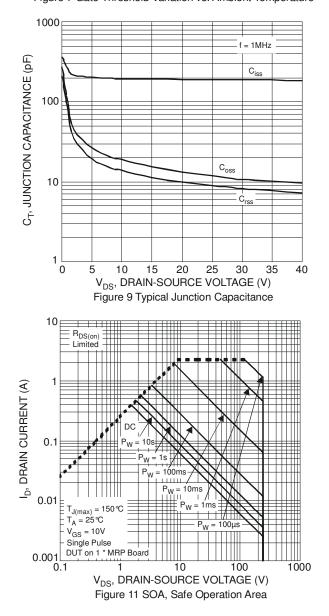


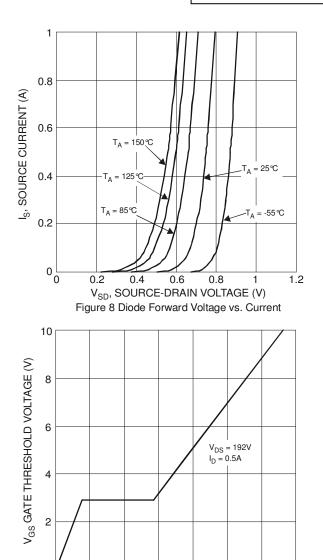
150











3

2

4

Q<sub>g</sub>, TOTAL GATE CHARGE (nC) Figure 10 Gate Charge

5

6

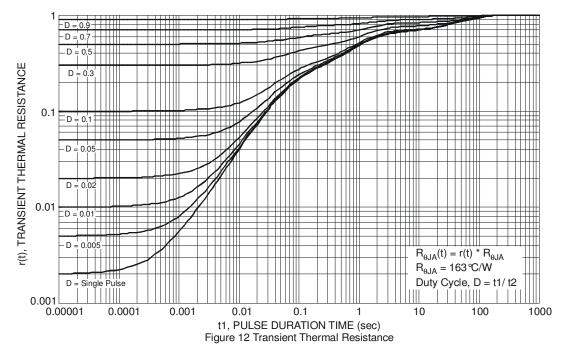
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0

0

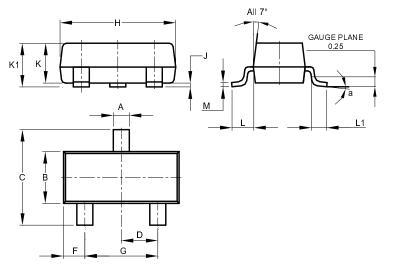
1





# Package Outline Dimensions

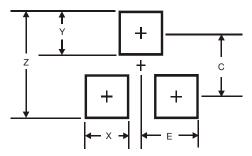
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
К	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а		8°				
All	Dimens	ions in	mm			

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35

DMN24H3D5L Document number: DS37270 Rev. 3 - 2



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